

# **HHS Public Access**

Author manuscript *IEEE J Solid-State Circuits*. Author manuscript; available in PMC 2022 June 01.

#### Published in final edited form as:

IEEE J Solid-State Circuits. 2021 June ; 56(6): 1837–1848. doi:10.1109/jssc.2020.3042962.

# A 3.5 mV Input Single-Inductor Self-Starting Boost Converter with Loss-Aware MPPT for Efficient Autonomous Body-Heat Energy Harvesting

## Soumya Bose [Student Member, IEEE],

School of Electrical Engineering and Computer Science, Oregon State University, Corvallis, OR 97331, USA

## Tejasvi Anand [Member, IEEE],

School of Electrical Engineering and Computer Science, Oregon State University, Corvallis, OR 97331 USA

#### Matthew L. Johnston [Member, IEEE]

School of Electrical Engineering and Computer Science, Oregon State University, Corvallis, OR 97331 USA

# Abstract

A single-inductor self-starting boost converter is presented suitable for thermoelectric energy harvesting from human body heat. In order to extract maximum energy from a thermoelectric generator (TEG) at small temperature gradients, a loss-aware maximum power point tracking (MPPT) scheme was developed that enables the harvester to achieve high end-to-end efficiency at low input voltages. The boost converter is implemented in a 0.18 µm CMOS technology and is more than 75% efficient for a matched input voltage range of 15 mV–100 mV, with a peak efficiency of 82%. Enhanced power extraction enables the converter to sustain operation at an input voltage as low as 3.5 mV. In addition, the boost converter self-starts with a minimum TEG voltage of 50 mV leveraging a dual-path architecture without using additional off-chip components.

#### Keywords

DC-DC boost converter; thermoelectric generator; body heat; energy harvesting; cold-start; battery-less

# I. INTRODUCTION

ENERGY harvesting can be used to power wireless sensor nodes for realizing fully autonomous networks [1], or for powering miniaturized, self-sustaining wearable devices for preventive healthcare and continuous vital sign monitoring [2]. Microwatt-scale power

He is now with Intel, Hillsboro, OR 97124 USA (boseso@oregonstate.edu).

Personal use is permitted, but republication/redistribution requires IEEE permission., See http://www.ieee.org/publicationsstandards/publications/rights/index.html for more information.

extracted from human body heat using thermoelectric generators (TEG) can provide such power autonomy efficiently, and this approach excels in indoor environments where other energy sources, such as solar energy, are less abundant. However, the small temperature gradient (T) of a few degrees between the skin surface and the ambient environment generates only a few tens of millivolts of open-circuit voltage from a centimeter scale TEG; impedance matching for maximum power transfer further reduces the input voltage to the DC-DC boost converter. This makes efficient power conversion especially challenging, and for fully autonomous applications, the converter must also self-start at this low input voltage.

In recent years, a variety of DC-DC boost converter architectures have been reported to address the challenges posed by low input voltage. One such boost converter designed for thermoelectric energy harvesting can operate with an input voltage as low as 20 mV [3]. However, this architecture lacks maximum power point tracking (MPPT), reducing the total extracted output power of the harvester despite high converter efficiency; the design also requires an additional source of energy for initial start-up of the converter. Boost converter architectures sustaining operation with an input voltage as low as 10 mV have also been demonstrated [4], [5], but these approaches also fail to self-start at low input voltage, making them unsuitable for fully battery-less energy harvesting.

For low-voltage self-start, off-chip transformers have been exploited to start a boost converter at tens of millivolts from a TEG [6], [7]; however, the implementation in [6] for high resistance TEGs is not capable of generating microwatts of power from low temperature differential (e.g. body-heat), whereas transformer reuse in [7] restricts the efficiency of the converter to 61%. High peak efficiency and low-voltage cold-start of the boost converter is demonstrated in both [8] and [9], but these require multiple inductors, increasing the form-factor and off-chip component count for the harvester. Cold-start of the boost converter at 70 mV in [10] and at 57 mV in [11] are achieved by means of integrated self-start techniques, but overall converter efficiency is comparatively low. Hence, it is evident that high efficiency and self-start of the converter at low voltages are fundamentally difficult problems to address using a single architecture and requires further investigation.

In this work, we present a single-inductor boost converter architecture that is capable of harvesting energy efficiently and can also self-start at low voltage from a thermoelectric generator [12]. A unique loss-aware maximum power point tracking (MPPT) scheme is proposed that reduces the total losses of the boost converter while ensuring maximum power transfer (MPT) from the source to the input, improving the end-to-end efficiency and output power of the harvester. The boost converter delivers power to the output with more than 75% efficiency at input voltages above 15 mV, and it achieves a peak efficiency of 82% with 50 mV input. Efficient low-voltage operation of the converter enables sustained operation at an input voltage as low as 3.5 mV. In addition, a dual path architecture is proposed which assists in self-starting the converter with an input voltage as low as 50 mV, without requiring additional off-chip components. The harvester generates a regulated output voltage of 1.2 V and operates over a TEG output voltage range of 7 mV–200 mV.

The rest of the paper is organized as follows: Section II describes the boost converter architecture and theoretical basis of loss-optimized maximum power transfer; Section III

explains detailed circuit implementations and design methodology; performance of the fabricated chip is presented in Section IV; and, Section V provides a brief conclusion.

# II. SELF-STARTING BOOST CONVERTER ARCHITECTURE

A TEG generates voltage,  $V_{TG}$ , proportional to the *T* between human skin and environment with only a few ohms of source resistance,  $R_{TG}$ . A dual-path DC-DC converter architecture is implemented to boost the voltage as shown in Fig. 1 by utilizing a single offchip inductor to achieve efficient power conversion as well as low-voltage self-start.

#### A. Low-voltage self-start and dual-path operation

A one-shot cold-start technique demonstrating fast and low-voltage cold-start of a boost converter is adopted for self-start [11]. During cold-start, as shown in Fig. 2a, a charge-pump-based on-chip voltage multiplier clocked by a low-voltage ring oscillator boosts the input voltage  $V_{\text{IN}}$ . The boosted output of the charge pump,  $V_{\text{CP}}$ , is used to generate a single start-up strobe pulse,  $V_{\text{ST}}$ . This pulse turns on the start-up low side switch,  $M_{\text{ST}}$ , for a small duration, which charges the inductor, L, with current from the TEG.

On the falling edge of  $V_{ST}$ , inductive overshoot at  $V_S$  turns on the PMOS diode,  $M_D$ , asynchronously and the inductor current charges the on-chip storage capacitor,  $C_{INT}$ . This intermediate storage capacitor is chosen small enough (200 pF) so that energy accumulated during the strobe cycle can charge it sufficiently to generate a voltage,  $V_{INT}$ , momentarily higher than 500 mV following the falling edge of  $V_{ST}$ . A secondary oscillator (OSC) powered by  $V_{INT}$  starts operation and generates a switching clock, CK, to continue operation of the inductive boost converter. Now the inductor is energized with more current every CK cycle using a wider low-side switch,  $M_{LS}$ , as shown in Fig. 2b, and energy is transferred to  $C_{INT}$ ; this is an asynchronous mode of operation. A voltage regulation block is also activated in this phase to track  $V_{INT}$ .

A power-on-reset (POR1) circuit senses the rise of  $V_{\rm INT}$  and turns on switch  $S_1$  as soon as  $V_{\rm INT}$  crosses 1V. As shown in Fig. 2c, this activates a secondary path of inductor energy transfer, which operates synchronously using a high-side PMOS switch,  $M_{\rm HS}$ , and powers the final output,  $V_{\rm OUT}$ . The *n*-well of  $M_{\rm HS}$  (and of  $M_{\rm D}$ ) is always biased to the highest potential using dynamic body biasing (DBB) to avoid inefficient body-current (Fig. 1).  $S_1$ , implemented using a PMOS transistor, is held off in the previous phases utilizing the charge pump output,  $V_{\rm CP}$ , and restricts the start-up energy of the inductor from flowing to the synchronous path on the falling edge of  $V_{\rm ST}$ . This helps in kick-starting the asynchronous path with a relatively small amount of energy and accelerates the overall start-up process. With low available TEG power, discontinuous conduction mode (DCM) operation is used for synchronous boost conversion [13], implemented by a zero current sensing (ZCS) block to adjust the on-time,  $t_{\rm HS}$ , of  $M_{\rm HS}$ .

During this handover phase, illustrated in Fig. 2c, the high-efficiency synchronous path charges the output capacitor,  $C_{OUT}$  (1uF), while the asynchronous path provides power to the control circuits. The dual paths are operated in a time-multiplexed manner by means of a dead-time, t, between  $t_{LS}$  and  $t_{HS}$ . Output, *EN*, of the voltage regulation block, which

monitors  $V_{\rm INT}$ , enables t to force  $M_{\rm D}$  to turn on briefly; the inductor current is rerouted to the asynchronous path during this dead time and recharges  $C_{\rm INT}$ . With the falling edge of  $CK_{\rm HS}$ , as  $M_{\rm HS}$  is turned on, the inductor current reverts back to the synchronous path to charge  $C_{\rm OUT}$ .

Finally, as  $V_{\text{OUT}}$  crosses 0.7V, detected by POR2, the PMOS power switch  $S_2$  is turned on, shorting  $V_{\text{OUT}}$  and  $V_{\text{INT}}$ ; *t* is deactivated with the help of a multiplexer. As illustrated in Fig. 2d, the boost converter now operates in an exclusively synchronous mode to provide both control power and output power. The rising  $V_{\text{OUT}}$  disables the start-up clock and turns off the start-up voltage multiplier, avoiding unnecessary power consumption during normal operation of the boost converter. As *POR2* goes low, the *EN* signal from the same voltage regulation block is now utilized to enable/disable the switching clock and regulate  $V_{\text{OUT}}$  by means of an on-off hysteretic control scheme.

The proposed dual-path architecture utilizes the asynchronous path to speed up the start-up process, leveraging the one-shot cold-start mechanism, and ultimately starts a high-efficiency synchronous boost converter at low input voltage without requiring an additional off-chip inductor.

#### B. Boost converter losses and maximum power transfer

Efficiency of the boost converter and maximum power transfer at the input determine the final output power available to the load.

**1)** Losses in a DC-DC boost converter: The voltage conversion gain, *K*, of a boost converter operating in DCM mode is given as

$$K = \frac{V_{\text{OUT}}}{V_{\text{IN}}} = \left(1 + \frac{t_{\text{LS}}}{t_{\text{HS}}}\right),\tag{1}$$

where  $t_{LS}$  and  $t_{HS}$  are the on-times of  $M_{LS}$  and  $M_{HS}$  respectively as shown in Fig. 3a. For applications with low  $V_{IN}$ , required K being large,  $t_{LS} \gg t_{HS}$ , and the input power,  $P_{IN}$ , flowing into the converter can be calculated as

$$P_{\rm IN} = \frac{1}{T} \cdot \frac{1}{2} \cdot V_{\rm IN} I_{\rm P}(t_{\rm LS} + t_{\rm HS}) \approx \frac{1}{2} \cdot \frac{V_{IN}^2 t_{LS}^2}{LT}$$
(2)

where *T* is the time period of the switching clock and  $I_{\rm P} = V_{\rm IN} t_{\rm LS}/L$  (when  $t_{\rm LS} \ll$  inductor charging time constant) is the peak inductor current. On the other hand, conduction power losses,  $P_{\rm C}$ , due to the on-resistance of  $M_{\rm LS}$  and  $M_{\rm HS}$  can be derived as

$$P_{\rm C} = P_{\rm C,LS} + P_{\rm C,HS}$$
  
=  $\frac{1}{3} \cdot \frac{I_P^2}{T} \cdot (R_{\rm LS} t_{\rm LS} + R_{\rm HS} t_{\rm HS}).$  (3)

By expressing  $t_{\rm HS}$  and  $I_{\rm P}$  in (3) in terms of  $t_{\rm LS}$ ,

$$P_{\rm C} = \frac{1}{3} \cdot \frac{V_{IN}^2 t_{LS}^3 R_{\rm C}}{L^2 T} \tag{4}$$

where  $R_{\rm C} = (R_{\rm LS} + R_{\rm HS}/K)$  represents the total conduction resistance contributed by LS and HS switches. For high values of *K*, conduction loss contributed by the LS path dominates.

Power consumed by the control circuits is mostly the switching power required for the drivers to drive the large LS and HS switches. If the total lumped switch gate capacitance of the control circuit is  $C_{SW}$ , the switching power is given as

$$P_{\rm SW} = C_{\rm S} V_{\rm OUT}^2 \cdot f_{\rm S} = C_{\rm S} K^2 V_{IN}^2 \cdot f_{\rm S} \tag{5}$$

where  $f_{\rm S} = 1/T$  is the switching frequency.

Additional power losses due to timing imperfections, leakage currents, and parasitic loading are small and can be neglected. Hence, the total power loss of the converter can be approximated as

$$P_{\rm LOSS} = P_{\rm C} + P_{\rm SW} = \frac{1}{3} \cdot \frac{V_{IN}^2 t_{\rm LS}^3 R_{\rm C}}{L^2 T} + C_{\rm S} K^2 V_{IN}^2 \cdot f_{\rm S} \,. \tag{6}$$

The loss of the converter when normalized with input power (2) and expressed in terms of duty-cycle,  $D = t_{LS}/T$ , as

$$\frac{P_{\rm LOSS}}{P_{\rm IN}} = \frac{2DR_{\rm C}}{3L} \cdot \frac{1}{f_{\rm S}} + \frac{2C_{\rm S}K^2L}{D^2} \cdot f_{\rm S}^2,\tag{7}$$

exhibits concave behavior with respect to  $f_S$ , as plotted in Fig. 3b, where conduction loss dominates at lower  $f_S$  and switching loss dominates at higher  $f_S$ . With other parameters fixed, an optimal  $f_S$  minimizes  $P_{LOSS}/P_{IN}$  and thereby maximizes the efficiency of the DC-DC converter,  $\eta_{DCDC}$ , as

$$\eta_{\text{DCDC}} = \frac{P_{\text{IN}} - P_{\text{LOSS}}}{P_{\text{IN}}} = 1 - \frac{P_{\text{LOSS}}}{P_{\text{IN}}}$$
(8)

2) Maximum power transfer at input: The internal resistance,  $R_{TG}$ , of the TEG limits the amount of power that can be extracted from the generator. For maximum power transfer, the input resistance,  $R_{IN}$ , of the boost converter must be matched with  $R_{TG}$ . The extent of matching can be expressed as the efficiency of maximum power point tracking,  $\eta_{MPPT}$ , defined as the proportion of the theoretical maximum power ( $V_{TG}^2/4R_{TG}$ ) entering the converter. As a TEG operates as a linear source for small values of T[14],  $R_{TG}$  can be assumed constant for body-heat energy harvesting applications, and one-time tuning of the power converter to set  $R_{IN} = R_{TG}$  is sufficient to ensure MPPT; this saves additional control power compared to continuous MPPT approaches [15].

The input resistance of a DC-DC boost converter operating in discontinuous conduction mode can be derived by calculating the average input current [16], [17], and can be expressed in terms of duty-cycle, D, as  $R_{IN} \approx (2Lf_S)/D^2$ . Hence, for a fixed value of L and D, input matching can be achieved by tuning the  $f_S$  of the switching clock, as shown in Fig. 3c.

#### C. Loss-optimized maximum power point tracking

Although a fixed  $f_S$  of the switching clock with D = 0.5 can assure maximum power transfer at the input, it may not be the optimal frequency for the normalized loss and can result in a low conversion efficiency,  $\eta_{DCDC}$ . Similarly, the optimal value of  $f_S$  required to maximize  $\eta_{DCDC}$ , obtained from (7) at D = 0.5, can cause an input impedance mismatch and thereby reduce  $\eta_{MPPT}$ . The end-to-end efficiency of the harvester,  $\eta_{HARV}$ , is determined by the final output power as a proportion of the available input power and can be expressed as

$$\eta_{\text{HARV}} = \eta_{\text{MPPT}} \times \eta_{\text{DCDC}} \,. \tag{9}$$

As such, input matching using  $f_{\rm S}$ -only tuning may not improve the overall output power of the harvester; the efficiency of the converter must be enhanced while assuring MPPT at the input. To mitigate this trade off, a loss-aware MPPT architecture was developed, where  $\eta_{\rm DCDC}$  is improved by reducing converter losses while keeping the input matched by tuning both *D* and  $f_{\rm S}$ ; this enhances the  $\eta_{\rm HARV}$  across the input voltage range and enables operation with  $V_{\rm IN}$  as low as a few millivolts.

At perfect input matching,  $R_{TG} = R_{IN}$ , normalized loss can be re-formulated using (7) as

$$\frac{P_{\text{LOSS}}}{P_{\text{IN}}} = \left(\frac{4R_{\text{C}}}{3R_{\text{TG}}}\right) \cdot \frac{1}{D} + \left(C_{\text{S}}K^2R_{\text{TG}}\right) \cdot f_{\text{S}}$$
(10)

Centimeter-scale TEGs have an internal resistance of a few ohms [14]. For moderately low TEG voltage (e.g. 50–200 mV) and corresponding conversion gain K, low duty-cycle results in higher conduction loss, as evident from (10). This is mainly due to an effective increase of conduction time,  $t_{LS}$ , at a lower value of  $f_S$  required for input matching. An increase in D, accompanied by a proportional increase in  $f_S$  to maintain the  $R_{IN}$  value for input matching, can effectively reduce the conduction time as illustrated in Fig. 4a, where the value of D is changed from 0.5 (red line) to 0.9 (blue line). The increase in  $f_S$  does not significantly affect the switching loss, as evident in Fig. 4b, due to the moderate value of K.

However, as the input voltage goes further lower, the required value of K becomes higher, and the same pair of  $(D, f_S)$  may no longer provide low loss, which impacts the overall converter efficiency. For TEG voltages below 40 mV, the input power is low enough that the switching power is comparable to the input power, and converter losses are dominated by the switching loss; this is also evident from (10). Lower  $f_S$  and D, as shown in Fig. 5a, are beneficial in this case to reduce the dominant switching loss without impacting the input MPPT. The resulting longer conduction time minimally affects losses due to small  $f_L$  at low

 $V_{\rm IN}$ . As shown in Fig. 5b, decreasing the duty-cycle from 0.9 to 0.5 can minimize the converter losses and improves  $\eta_{\rm DCDC}$  without impacting  $\eta_{\rm MPPT}$ .

Hence,  $\eta_{\text{HARV}}$  can be improved across a wide-range of TEG voltages by varying the dutycycle and frequency of the converter clock. While continuous loss-optimization could be achieved in theory, in this work we have implemented a loss-aware MPPT scheme using an adaptive clock whose duty-cycle and frequency are switched between discrete pairs of  $(D, f_S)$ for input matching based on the dominant losses of the converter at moderate and very-low TEG voltages applicable for body-heat energy harvesting applications.

# **III. CIRCUIT IMPLEMENTATIONS**

A low-voltage, self-starting boost converter requires startup circuits that function at voltages well below the threshold of transistor with minimal conduction, along with reduced leakage control circuits to make the converter efficient.

#### A. Ultra-low-voltage integrated cold-start

A voltage multiplier is needed to step up the small input voltage and power the control circuits of the inductive converter during start-up [8], [10], [18]. On-chip voltage multiplication using charge pumps at small input supply is challenging due to the ultra-sub-threshold conduction of the switches. A high-gate boosting technique demonstrated in [11] improves the gate overdrive of the switches to enhance conduction at small supply; however, this approach requires multiple charge pumps, which consumes more area. In this work, a single charge pump is used to achieve similarly boosted overdrive for the charge transfer switches (CTS) during the conduction phases of the charge pump stages.

A dual gate-boosting architecture is shown in Fig. 6a, where the initial stages of the charge pump use deep-*n*-well NMOS switches and the later stages use PMOS switches for charge transfer. The charge pump is a dual-phased Dickson architecture [19] with 15 stages in total. Higher voltages from later stages are fed back to improve gate overdrive of the NMOS switches of earlier stages; at the same time, lower voltages from earlier stages are utilized to improve the gate overdrive of PMOS switches of later stages. The dual gate boosting action using internal nodes eliminates the need for additional charge pump stages.

The gate-boosting action of the switches is done symmetrically, where the output nodes of stages 1 & 9, stages 2 & 10, and so forth, are used to generate gate drive for the respective CTSs. As shown in Fig. 6b, dual-phased voltages, P2 and P2B at the output of stage 2 and P10 and P10B at the output of stage 10 are used to generate gate clocks G2 - G2B and G9 - G9B, respectively, using dynamic inverters D1 - D4. The gate clocks for the second stage, G1 and G1B, are reused in the first stage with appropriate phasing to avoid additional charge pump stages. The final stage of the charge pump uses a diode-connected deep-*n*-well NMOS to avoid reverse charge flow during a voltage droop at the output. The boosted gate clocks are non-overlapping with the pumping clock phases, CK and CKB, to avoid reverse charge flow between consecutive stages during non-charge-transfer phases. Non-overlapping phases of the internal dual-phased voltages, PX - PXB and NX - NXB, are generated using non-overlapping clocks and level shifters (NOV-LS).

A stacked-inverter based ring-oscillator [20] is used to generate an on-chip start-up clock at small input voltages. The stage capacitance is 22 pF to achieve low enough slow switching limit (SSL) output impedance,  $N_{\rm (Cf_S)}$  [21], with the minimum sized CTSs to minimize loading of the weakly driven gate clocks. It is important to note that although a high gate-boosting action takes place as the internal voltages gradually increases towards the steady-state value, initial voltage boosting is slow and depends only on the leakage current of the switches. However, usage of PMOS switches for the later stages allows boosting of the later stages quickly, which then boosts the NMOS switches; the circular action results in rapid dual gate boosting and fast build-up of the output voltage,  $V_{\rm CP}$ .

The boosted voltage,  $V_{CP}$ , is used to power a one-shot generator. The basic building block of the one-shot generator as implemented in [11] comprises a two-transistor reference generator, leakage-based comparator, and a thyristor-based delay element. It generates an output pulse with a sharp falling edge to create inductive overshoot at  $V_S$ , which kick starts the asynchronous path by forward biasing the PMOS diode  $M_D$ .

#### B. Zero current sensing for high-efficiency boost conversion

The synchronous boost converter is operated in DCM mode, favorable for low power operation [13], where the inductor is disconnected from the output once  $I_L$  reaches zero value to avoid reverse energy flow. A digital zero current sensing (ZCS) scheme is adopted to save power. Instead of using a comparator [22], a flip-flop-based sensing mechanism [3] is used. The ZCS circuit block, shown in Fig. 7a, employs a flip-flop to sample the voltage, V<sub>S</sub>, at the rising edge of CK<sub>HS,DEL</sub>, a delayed version of CK<sub>HS</sub>, and to track the zero point of  $I_L$ . It generates a high or low output signal corresponding to an overshoot or undershoot of  $V_{\rm S}$ , respectively, depending upon the status of  $I_{\rm L}$  around the zero-crossing point. The delay between  $CK_{HS}$  and  $CK_{HS,DEL}$  plays a critical role in sensing the transition of  $V_S$  and is chosen as 24 ns to make sure that there is sufficient time for the voltage to transition following the closure of the high-side PMOS switch on the rising edge of CK<sub>HS</sub>. As illustrated in Fig. 7b, a rising edge of  $CK_{HS,DEL}$  will sense a high  $V_S$  at the flip-flop input when the inductor energy is not yet fully transferred to the output and  $I_{\rm L}$  is still approaching the zero value; the resulting output,  $(INC/\overline{DEC})$ , increments a counter to create a longer delay between the falling edges of CKLS and CKLS.DEL using a programmable delay block. This generates a wider low phase of  $CK_{\rm HS}$  in the next cycle to improve the inductor energy transfer with a longer on-time of the HS switch. Conversely, a low in the  $INC/\overline{DEC}$  signal indicates that inductor energy is fully transferred to the output and reverse current has started to flow from the output capacitor toward the input; this directs the counter to decrement, reducing the on-time of the HS switch in the following cycle. At steady state, the counter value toggles between two adjacent values in consecutive clock cycles. In order to accommodate a wide range of input voltages, a 7-bit counter is used to generate the required  $t_{\rm HS}$  with the programmable delay block, comprising unit delay elements, each capable of delaying the input pulse by 24 ns. Conventional delay blocks using capacitive elements incur high switching power consumption and also result in high crow-bar current due to slow transitions. To avoid this, a low power unit delay element, as shown in Fig. 7a, was designed for the programmable delay block, where a resistive discharge path is used to create a delay in the falling edge of the input pulse only. The pull-up and pull-down paths of intermediate

inverters are controlled to reduce the crow-bar current during the delay time. Also, individual delay elements are enabled only when needed, saving power at low input voltages.

#### C. Variable clock generation for loss-aware MPPT

The proposed loss-aware MPPT requires selection of duty-cycle, D, and frequency,  $f_S$ , of the switching clock based on the input voltage to minimize overall losses of the converter while matching its input impedance to the source.

As implemented, the system supports two  $(D, f_S)$  pairs, and a threshold input voltage for selecting between them must be chosen based on dominant losses in each regime. To determine the dominant loss mechanisms across the input voltage range, the overall converter losses for a fixed inductor value are normalized to the input power from a portable TEG [14] and analyzed using transistor-level simulation of the complete energy harvester by varying the frequency of the switching clock with a duty-cycle of D = 0.5. A 100 µH shielded power inductor [23] is chosen for the converter based on the required start-up energy to be stored in the inductor during the strobe-cycle for one-shot cold-start operation [11]. With a TEG source resistance of approximately  $5\Omega$  and an inductor DC resistance of 110 m $\Omega$ , it is observed that switching losses dominate overall converter losses for TEG voltages below 40 mV. For higher source voltage, conduction losses start to dominate over the switching losses as the input power increases. From this assessment we have chosen a matched  $V_{IN}$  of 20 mV ( $V_{TEG} = 40$  mV) as the threshold value; below this value, the alternate  $(D, f_S)$  pair is used for the switching clock. In order to avoid rapid toggling of  $(D, f_S)$ near the threshold, a hysteretic guard-band is used, where  $V_{\rm IN}$  of 25 mV is chosen as the upper voltage threshold for changing  $(D, f_S)$ .

For determination of *D* and  $f_S$  values needed to maximize end-to-end efficiency of the harvester across the input voltage range, normalized losses of the converter were analyzed by varying the duty-cycle of the switching clock parametrically with frequency. Based on that analysis, a duty-cycle of D = 0.55 and a frequency  $f_S = 8.33$  kHz were chosen for the switching clock at input voltage below 20 mV to match the input impedance with minimized losses of the converter. For higher input voltage, as the input power increases, a higher duty-cycle is needed, with the corresponding higher frequency required for MPPT. However, for higher values of  $V_{IN}$ , the voltage conversion ratio, *K*, reduces, as does the ratio  $t_{LS}/t_{HS}$ . This limits the maximum allowable *D* that ensures DCM operation such that  $t_{LS} + t_{HS} = 1/f_S$ . As such, a duty-cycle of D = 0.91 and frequency of  $f_S = 25$  kHz were selected for use at higher input voltages. Although this selection changes the input impedance value marginally compared to that with the chosen ( $D, f_S$ ) pair for  $V_{IN} < 20$  mV, the impact of this input voltage range.

Direct, continuous sensing of  $V_{IN}$  requires additional power consumption and further increases losses. As an alternative,  $t_{HS}$  can be used as a proxy indicator, as it is directly proportional to  $V_{IN}$  as long as  $V_{OUT}$  and  $t_{LS}$  are fixed (1). As shown in Fig. 7a, the counter code in the ZCS circuit, XO-X6, sets the required  $t_{HS}$  for each  $V_{IN}$  and hence can be re-used to achieve comprehensive  $V_{IN}$  tracking obviating the need for additional circuitry. The ZCS

code is utilized to select the appropriate  $(D, f_S)$  pair for the switching clock, *CK*, using a low-power digital circuit, shown in Fig. 8a.

A digital look up table, as shown in Fig. 8a, comprises a series of flip-flops and combinational logic to generate clocks with different combinations of duty-cycle and frequency. As shown, 16 flip-flop stages form a frequency divider and can generate frequencies between  $f_0/16$  to  $f_0/2$ , where  $f_0$  denotes the base clock frequency. Consecutive positive and negative edge-triggered flip-flops are used to create a wide range of duty-cycle by tapping the intermediate outputs and combining them with OR gates. A duty-cycle of  $0.5\pm n/2K_f$  is generated for even values of *n*, and  $0.5\pm(n-1+2D_0)/2K_f$  for odd values of *n*, where  $D_0$  denotes the base clock duty-cycle,  $K_f$  denotes the frequency division factor, and *n* can be any code between zero and  $(K_f - 1)$ . A base clock with  $f_0$  of 100 kHz and  $D_0 = 0.67$  is generated using a low-power oscillator architecture [24], primarily designed to initiate and operate the asynchronous converter (OSC in Fig. 1).

From the wide range of available values of  $(D, f_S)$ , the required pair variants are generated by selecting the corresponding code stored in a programmable register. Additionally, tunability of  $D_0$  and  $f_0$  of the base clock using separate control bits provides further flexibility for fine-tuning *CK* to calibrate out any static variation of  $R_{TG}$  for different TEG parts.

Fig. 8b illustrates selection of the  $(D, f_S)$  pair with transient variation of  $V_{IN}$  near the threshold. For  $V_{IN} > 20$  mV, the charging time of the inductor,  $t_{LS}$ , is equal to 36.67 µs. As  $V_{IN}$  decreases to 20 mV, the ZCS code required to generate the corresponding  $t_{HS}$  becomes 20, as illustrated in Fig. 8b. A decoder detects this and selects the lower  $(D, f_S)$  pair using the digital look up table. At this point,  $t_{LS}$  is 66.67 µs and the ZCS code threshold required to generate the  $t_{HS}$  for  $V_{IN}=25$  mV with the same delay elements becomes 46. Now the  $(D, f_S)$  pair reverts to the higher values. As  $t_{LS}$  reverts to 36.67 µs, the ZCS code would gradually converge to 25 to generate the  $t_{HS}$  required for  $V_{IN} = 25$  mV; the ZCS code being still higher than 20 (lower threshold), the  $(D, f_S)$  around a single threshold without adding complexity to the the ZCS circuit. The hysteresis is implemented with a simple RS latch to set or reset the value of  $(D, f_S)$  based on the decoder output.

While implemented here using two pairs, in future work the number of discrete  $(D, f_S)$  pairs and associated input voltage regions could be increased to further enhance efficiency across a wide input voltage range.

#### D. Dual-path operation and output voltage regulation

The dual-path operation of the boost converter during startup is made possible with the help of a voltage regulation block activated immediately following the one-shot cold start. As shown in Fig. 9a, a switched capacitor voltage divider divides the intermediate boosted voltage,  $V_{\rm INT}$ , to  $V_{\rm INT}/2$ , which is compared against two reference voltages,  $V_{\rm REF,LO}$  and  $V_{\rm REF,HI}$ , generated using ultra-low-power on-chip reference generators [25]. During start-up, this information is used to control (on/off) the dead-time, *t*, between  $CK_{\rm LS}$  and  $CK_{\rm HS}$ . This *t* forces the inductor current to flow through the diode  $M_{\rm D}$  for a short time to recharge

 $V_{\rm INT}$ , as illustrated in Fig. 9b, before the current is steered back to  $V_{\rm OUT}$ ; this continues

until  $V_{\text{OUT}}$  crosses 0.7V and is shorted to  $V_{\text{INT}}$  with a low *POR*<sup>2</sup> signal. During fully synchronous operation, the same control loop regulates  $V_{\text{OUT}}$  by enabling or disabling the switching clock, resulting in an energy-efficient hysteretic mode of voltage regulation.

# IV. MEASUREMENTS

The energy harvester was implemented in a 0.18  $\mu$ m CMOS process. A die micrograph is shown in Fig. 10; the converter circuits occupy an active area of 1.02mm<sup>2</sup>.

Electrical performance of the chip was characterized using a bench-top power supply with an added series resistance of 5 $\Omega$ , equivalent to the  $R_{TG}$  of a centimeter-scale TEG. Measured start-up transients, shown in Fig. 11a, demonstrate self-start of the boost converter with a minimum TEG voltage ( $V_{TG}$ ) of 50 mV. At this input voltage, it takes 252 ms from cold start for  $V_{OUT}$  to reach 1.2V with an off-chip output capacitor of 1  $\mu$ F. With higher  $V_{TG}$ , the output power of the start-up charge pump increases, and the start-up time decreases as shown in Table I.

A magnified region of the transient waveforms in Fig. 11b shows the parallel operation of the asynchronous and synchronous paths of the boost converter during start-up. The falling edge of the strobe triggers the asynchronous path, which feeds power to the control circuits for the synchronous path. As  $V_{INT}$  crosses 1V, the synchronous path is enabled and the inductor energy is fully shared by the two paths. Once  $V_{INT}$  crosses  $V_{REF,HI}$  it is regulated by the dead-time-based enable/disable control until  $V_{OUT}$  is shorted with it and the converter enters into high-efficiency, fully-synchronous conversion mode. The MPPT is enabled only after this point, and the hysteretic on-off voltage regulation regulates  $V_{OUT}$  at 1.2V.

A measured transient plot in Fig. 12 demonstrates the operation of the proposed MPPT scheme using adaptive duty-cycle and frequency of the switching clock. As shown, transition of the TEG voltage from 15 mV to 50 mV results in a change of the (D,  $f_s$ ) pair of the switching clock to optimize the efficiency of the converter. The switching clock with the new (D,  $f_s$ ) pair still tracks the maximum power point at the input of the converter by matching  $R_{\rm IN}$  with  $R_{\rm TG}$ , evident by a measured  $V_{\rm IN} = V_{\rm TG}/2$ .

Load and line regulation of the boost converter output are shown in Fig. 13.  $V_{OUT}$  is regulated at 1.2V with a step in the load current,  $I_{LOAD}$ , from 1 µA to 60 µA and then to 10 µA, and also when  $V_{TG}$  is changed among 20 mV, 50 mV, and 80 mV. The output voltage ripple depends on the difference between the two on-chip reference voltages used for hysteretic on-off regulation, and the frequency of the ripple depends on the available power from  $V_{TG}$ , drawn  $I_{LOAD}$ , and the size of  $C_L$ .

The efficiency of the boost converter was measured using a source meter (Keithley 4120) as current load. The maximum available output power for different values of  $V_{TG}$  was measured by varying  $I_{LOAD}$  for each  $V_{TG}$  and ratioed with the input power to plot the variation of the efficiency of the boost converter with TEG voltages, as shown in Fig. 14. The converter achieves an efficiency ( $\eta_{DCDC}$ ) of more than 75% for a  $V_{TG}$  above 30 mV ( $V_{IN}$  above 15 mV). The  $\eta_{DCDC}$  achieves a peak value of 82% with  $V_{TG} = 100$  mV. The corresponding peak end-to-end efficiency of the harvester ( $\eta_{HARV}$ ) is 80%.

Once started, high  $\eta_{\text{HARV}}$  at low input voltage enables the converter to sustain operation at a  $V_{\text{IN}}$  as low as 3.5 mV as shown in Fig. 15, thanks to the loss-aware MPPT scheme. Below this  $V_{\text{IN}}$ , losses exceed available power and the converter stops operation. Utilization of the harvester power at a TEG voltage of 15 mV is shown in Fig. 16. The converter consumes a measured quiescent current of 470 nA at a  $V_{\text{TG}}$  of 50 mV, which scales down to 240 nA for a  $V_{\text{TG}}$  of 7 mV by means of the adaptive duty-cycle and frequency of the switching clock.

The performance of the implemented harvester is compared alongside state-of-the-art thermoelectric harvesters in Table II.

When tested with a commercial TEG (Marlow TG12–6-01L), the harvester self-starts with a *T* of just 1.4°C and sustains operation until the *T* between the skin surface and ambient environment falls below 0.2°C. The experimental setup is shown in Fig. 17. The minimum TEG voltage required to self-start the harvester is tested across 7 chips, and the measured value varies between 48 mV and 53 mV.

# V. CONCLUSION

A single-inductor boost converter is demonstrated capable of achieving high efficiency at low input voltage from a TEG attached to human body. Enhanced efficiency of the converter while ensuring maximum power transfer at the input enables the complete harvester to achieve high end-to-end efficiency across the input voltage range by means of a loss-aware MPPT scheme by changing the duty-cycle and frequency of the switching clock. This not only helps to achieve peak efficiency at lower input voltage but also enables the harvester to sustain operation at a voltage as low as 7 mV from the TEG which corresponds to a T of  $0.2^{\circ}$ C.

One-shot integrated cold-start along with a dual-path converter architecture achieves low voltage (50 mV) start-up and makes the harvester completely autonomous, removing the need for a battery at any stage of operation. These features together make the implemented TEG-based harvester ideal for powering energy-efficient wearables using human body heat.

#### Acknowledgments

This work was supported in part by the National Institutes of Health under Awards R21DE027170 and R01EB028104.

# Biography



**Soumya Bose** (S'16) received the B.E. degree in electronics and telecommunication engineering from the Indian Institute of Engineering Science & Technology (IIEST), Shibpur, India, in 2009, the M.Tech. degree from Indian Institute of Technology (IIT),

Kharagpur, India, in 2013, and the Ph.D degree in electrical and computer engineering from Oregon State University, Corvallis, OR, USA in 2019.

From 2013 to 2015, he was with Rambus, Bengaluru, India, working on high-speed memory interfaces for multi-protocol PHYs. From May 2018 to August 2018, he was with Kilby Labs, Texas Instruments, Dallas, TX, USA, where he worked on ultra-low quiescent current low-dropout (LDO) regulator. He is currently with Intel Corporation, Hillsboro, OR, USA, developing power delivery circuits for next generation SoCs. His research interests include low-power circuit design for analog signal processing, bio-medical sensor interfaces, energy harvesting and power management.

Dr. Bose received the Center for Design of Analog-Digital Integrated Circuits (CDADIC) Best Poster Award in 2017. He also serves as a Reviewer for the IEEE JOURNAL OF SOLID-STATE CIRCUITS, and IEEE TRANSACTIONS ON CIRCUITS AND SYSTEMS I & II.



**Tejasvi Anand** Tejasvi Anand (S'12–M'15) is an Assistant Professor in the department of Electrical Engineering and Computer Science at the Oregon State University, Corvallis, OR, USA.He received his Ph.D. degree in Electrical Engineering from the University of Illinois at Urbana-Champaign, IL, USA in 2015, and M.Tech. degree (distinction) in Electronics Design and Technology from the Indian Institute of Science, Bangalore, India, in 2008. From 2008 to 2010, he worked as an Analog Design Engineer at Cosmic Circuits (now Cadence), Bangalore. His research focuses on wireline communication, energy harvesters, and frequency synthesizers with an emphasis on energy efficiency.

Dr. Anand is a recipient of 2014–15 IEEE Solid-State Circuits Society Predoctoral Achievement Award, 2015 Broadcom Foundation University Research Competition Award (BFURC), 2015 M. E. Van Valkenburg Graduate Research Award from the University of Illinois, 2013 Analog Devices Outstanding Student Designer Award, 2009 CEDT Design (Gold) Medal from the Indian Institute of Science, Bangalore, India. Dr. Anand serves as a Technical Committee Member of Custom Integrated Circuits Conference (CICC).



**Matthew L. Johnston** (S'03–M'12) received the B.S. degree in electrical engineering from the California Institute of Technology, Pasadena, CA, USA, in 2005, and the M.S. and Ph.D.

degrees in electrical engineering from Columbia University, New York, NY, USA, in 2006 and 2012, respectively.

He was a Co-Founder and the Manager of Research with Helixis, Carlsbad, CA, USA, a Caltech-based spinout developing instrumentation for real-time DNA amplification, from 2007 to its acquisition by Illumina, San Diego, CA, USA, in 2010. From 2012 to 2013, he was a Post-Doctoral Scholar with the Bioelectronic Systems Lab, Columbia University. In 2014, he joined Oregon State University, Corvallis, OR, USA, where he is currently an Associate Professor with the School of Electrical Engineering and Computer Science. His current research interests include the integration of sensors and transducers with silicon integrated circuits, stretchable circuits and sensor systems, lab-on-CMOS platforms, bio-energy harvesting, and low-power distributed sensing.

Dr. Johnston was the recipient of the 2020 Semiconductor Research Corporation (SRC) Young Faculty Award. He is currently an Associate Editor of the IEEE TRANSACTIONS ON BIOMEDICAL CIRCUITS AND SYSTEMS and the IEEE OPEN JOURNAL OF CIRCUITS AND SYSTEMS. He also serves on the Biomedical and Life Science Circuits and Systems Technical Committee and the Analog Signal Processing Technical Committee of the IEEE Circuits and Systems Society.

# REFERENCES

- [1]. Warneke BA, Scott MD, Leibowitz BS, Lixia Zhou CL Bellew JA Chediak JM Kahn BE Boser, and Pister KSJ, "An autonomous 16 mm3 solar-powered node for distributed wireless sensor networks," in SENSORS, 2002 IEEE, vol. 2, June 2002, pp. 1510–1515 vol.2.
- [2]. Leonov V, "Thermoelectric energy harvesting of human body heat for wearable sensors," IEEE Sensors Journal, vol. 13, no. 6, pp. 2284–2291, 6 2013.
- [3]. Carlson EJ, Strunz K, and Otis BP, "A 20 mV input boost converter with efficient digital control for thermoelectric energy harvesting," IEEE Journal of Solid-State Circuits, vol. 45, no. 4, pp. 741–750, 4 2010.
- [4]. Shrivastava A, Roberts NE, Khan OU, Wentzloff DD, and Calhoun BH, "A 10 mV-input boost converter with inductor peak current control and zero detection for thermoelectric and solar energy harvesting with 220 mV cold-start and-14.5 dBm, 915 MHz RF kick-start," IEEE Journal of Solid-State Circuits, vol. 50, no. 8, pp. 1820–1832, 8 2015.
- [5]. Luo Z, Zeng L, Lau B, Lian Y, and Heng C, "A sub-10 mV power converter with fully integrated self-start, MPPT, and ZCS control for thermoelectric energy harvesting," IEEE Transactions on Circuits and Systems I: Regular Papers, vol. 65, no. 5, pp. 1744–1757, 5 2018.
- [6]. Teh Y and Mok PKT, "Design of transformer-based boost converter for high internal resistance energy harvesting sources with 21 mV self-startup voltage and 74% power efficiency," IEEE Journal of Solid-State Circuits, vol. 49, no. 11, pp. 2694–2704, 11 2014.
- [7]. Im J, Wang S, Ryu S, and Cho G, "A 40 mV transformer-reuse self-startup boost converter with MPPT control for thermoelectric energy harvesting," IEEE Journal of Solid-State Circuits, vol. 47, no. 12, pp. 3055–3067, 12 2012.
- [8]. Weng P, Tang H, Ku P, and Lu L, "50 mV-input batteryless boost converter for thermal energy harvesting," IEEE Journal of Solid-State Circuits, vol. 48, no. 4, pp. 1031–1041, 4 2013.
- [9]. Lim B, Seo J, and Lee S, "A colpitts oscillator-based self-starting boost converter for thermoelectric energy harvesting with 40-mV startup voltage and 75% maximum efficiency," IEEE Journal of Solid-State Circuits, pp. 1–10, 2018.
- [10]. Goeppert J and Manoli Y, "Fully integrated startup at 70 mV of boost converters for thermoelectric energy harvesting," IEEE Journal of Solid-State Circuits, vol. 51, no. 7, pp. 1716– 1726, 7 2016.

- [11]. Bose S, Anand T, and Johnston ML, "Integrated cold start of a boost converter at 57 mV using cross-coupled complementary charge pumps and ultra-low-voltage ring oscillator," IEEE Journal of Solid-State Circuits, vol. 54, no. 10, pp. 2867–2878, 10 2019. [PubMed: 31723304]
- [12]. Bose S, Anand T, and Johnston ML, "A 3.5 mV input, 82% peak efficiency boost converter with loss-optimized MPPT and 50 mV integrated cold-start for thermoelectric energy harvesting," in 2019 IEEE Custom Integrated Circuits Conference (CICC), April 2019, pp. 1–4.
- [13]. Zhou Xunwei, Donati M, Amoroso L, and Lee FC, "Improved light-load efficiency for synchronous rectifier voltage regulator module," IEEE Transactions on Power Electronics, vol. 15, no. 5, pp. 826–834, 9. 2000.
- [14]. Marlow thermoelectric generator (TEG) module TG12–2.5–01LS. Marlow Industries, Inc. [Online]. Available: https://cdn2.hubspot.net/hubfs/547732/DataSheets/TG12-2.5.pdf
- [15]. Liu X, Huang L, Ravichandran K, and Snchez-Sinencio E, "A highly efficient reconfigurable charge pump energy harvester with wide harvesting range and two-dimensional MPPT for internet of things," IEEE Journal of Solid-State Circuits, vol. 51, no. 5, pp. 1302–1312, 5 2016.
- [16]. Bandyopadhyay S and Chandrakasan AP, "Platform architecture for solar, thermal, and vibration energy combining with MPPT and single inductor," IEEE Journal of Solid-State Circuits, vol. 47, no. 9, pp. 2199–2215, 9. 2012.
- [17]. Chen S, Huang T, Ng SS, Lin K, Du M, Kang Y, Chen K, Wey C, Lin Y, Lee C, Lin J, and Tsai T, "A direct ACDC and DCDC cross-source energy harvesting circuit with analog iterating-based MPPT technique with 72.5% conversion efficiency and 94.6% tracking efficiency," IEEE Transactions on Power Electronics, vol. 31, no. 8, pp. 5885–5899, 2016.
- [18]. Chen P, Ishida K, Ikeuchi K, Zhang X, Honda K, Okuma Y, Ryu Y, Takamiya M, and Sakurai T, "Startup techniques for 95 mV stepup converter by capacitor pass-on scheme and V<sub>th</sub>-tuned oscillator with fixed charge programming," IEEE Journal of Solid-State Circuits, vol. 47, no. 5, pp. 1252–1260, 5 2012.
- [19]. Dickson JF, "On-chip high-voltage generation in MNOS integrated circuits using an improved voltage multiplier technique," IEEE Journal of Solid-State Circuits, vol. 11, no. 3, pp. 374–378, 6 1976.
- [20]. Bose S and Johnston ML, "A stacked-inverter ring oscillator for 50 mV fully-integrated cold-start of energy harvesters," in 2018 IEEE International Symposium on Circuits and Systems (ISCAS), May 2018, pp. 1–5.
- [21]. Seeman MD and Sanders SR, "Analysis and optimization of switched-capacitor DCDC converters," IEEE Transactions on Power Electronics, vol. 23, no. 2, pp. 841–851, 3 2008.
- [22]. Chowdary G, Singh A, and Chatterjee S, "An 18 nA, 87% efficient solar, vibration and RF energy-harvesting power management system with a single shared inductor," IEEE Journal of Solid-State Circuits, vol. 51, no. 10, pp. 2501–2513, 2016.
- [23]. SMT Shielded Power Inductor, 7447709101. Wurth Elektronik. [Online]. Available: https:// www.we-online.com/catalog/datasheet/7447709101.pdf
- [24]. Nadeau PM, Paidimarri A, and Chandrakasan AP, "Ultra low-energy relaxation oscillator with 230 fJ/cycle efficiency," IEEE Journal of Solid-State Circuits, vol. 51, no. 4, pp. 789–799, 2016.
- [25]. Lee I, Sylvester D, and Blaauw D, "A subthreshold voltage reference with scalable output voltage for low-power IoT systems," IEEE Journal of Solid-State Circuits, vol. 52, no. 5, pp. 1443–1449, 5 2017.
- [26]. Cao P, Qian Y, Xue P, Lu D, He J, and Hong Z, "A bipolar-input thermoelectric energyharvesting interface with boost/flyback hybrid converter and on-chip cold starter," IEEE Journal of Solid-State Circuits, pp. 1–13, 2019.



## Fig. 1.

Self-starting single-inductor boost converter architecture for low-voltage thermoelectric energy harvesting utilizing human body heat.

Bose et al.





Illustrated phases of operation of the energy harvester architecture: (a) cold-start operation, (b) asynchronous operation, (c) dual asynchronous and synchronous operation (handover phase), and (d) fully synchronous operation (primary boost conversion).



# Fig. 3.

(a) A boost converter operating in discontinuous conduction mode (DCM), (b) power loss of the converter normalized with the input power across varying frequency, and (c) tuning converter switching frequency to achieve input resistance matching for maximum power transfer.

Author Manuscript



## Fig. 4.

(a) Reduction in the charging time and peak current of the inductor resulting from an increase of  $f_S$  and D of the switching clock, without impacting input impedance matching. (b) Corresponding decrease in the overall losses of the converter for source voltages above 50 mV, normalized with the input power, due to smaller conduction losses.

Author Manuscript



#### Fig. 5.

(a) Reduction of  $f_S$  at very low source voltage (<40 mV) reduces the dominant switching losses and is accompanied by a proportional decrease in *D* to ensure MPPT. (b) Corresponding improvement in the overall converter losses normalized with the input power.



# Fig. 6.

(a) One-shot start-up with on-chip voltage multiplier. (b) High dual gate-boosting using internal voltages and both NMOS and PMOS switches.





(a) Implementation of zero current sensing (ZCS) using digital sensing and (b) timing diagram showing operation of ZCS.





(a) Implementation of loss-aware MPPT using digital circuits. (b) Timing diagram showing adaptive duty-cycle and frequency of the switching clock for optimizing loss of the converter while ensuring maximum input power transfer.





(a) Hysteretic on-off voltage regulation using on-chip voltage references. (b) Timemultiplexed, dual-path operation of the single-inductor DC-DC boost converter during startup.



**Fig. 10.** Die photo of the chip fabricated in 0.18 μm CMOS technology.







#### Fig. 11.

(a) Measured start-up transients demonstrate self-start of the boost converter with minimum input voltage of 50 mV, and (b) zoomed waveform shows one-shot triggered cold-start sequences, including parallel asynchronous-synchronous operation of the single-inductor boost converter.



# Fig. 12.

Measured transients showing adaptive change of duty-cycle and frequency of switching clock with variation of input voltage for loss-aware MPPT at the input of the converter.







**Fig. 14.** Measured efficiency of the boost converter for different TEG voltages.



#### Fig. 15.

Measured transients showing operation of the converter at the lowest input voltage of 3.5 mV with an output regulated voltage of 1.2 V.



# Fig. 16.

Power distribution at  $V_{TG} = 15$  mV: (a) measured output power with estimated loss and (b) break-down of control power by block.







#### TABLE I

STARTUP TIMES AT DIFFERENT SOURCE VOLTAGES

Source voltage	Startup time
50 mV	252 ms
75 mV	42 ms
100 mV	21 ms

Author Manuscript

# TABLE II

PERFORMANCE COMPARISON WITH STATE-OF-THE-ART THERMOELECTRIC ENERGY HARVESTERS

5] JSSC'16 [10] JSSC'19 [26] This work	0.13 µm 0.18 µm 0.18 µm	On-chip On-chip On-chip	70 mV 129 mV <b>50 mV</b>	1.5 s 150 s (1) 252 ms	- 50 mV 7 mV	1.25 V 0.8 V <b>1.2 V</b>	Yes/Yes Yes/Yes Yes/Yes	<b>5</b> 9% 84% <b>80%</b>	- 23% 58%	_
TCAS'18 [5	65nm	On-chip	210 mV	2.3 s <sup>(1)</sup>	14 mV	1.4 V	Yes/Yes	71.5%	%05	
JSSC'15 [4]	0.13 µm	On-chip	220 mV	3.5 s <sup>(1)</sup>	20 mV	1.1 V	No/Yes	83% (2)	21% (2)	•
JSSC'12 [7]	0.13 µm	Off-chip	40 mV	22 s <sup>(1)</sup>	ı	2 V	Yes/Yes	61%	32%	Ŧ
JSSC'18 [9]	65nm	Off-chip	40 mV	180 ms <sup>(1)</sup>	40 mV	1.1 V	Yes/Yes	75%	12%	,
JSSC'13 [8]	65nm	Off-chip	50 mV	22 ms <sup>(1)</sup>	30 mV	1.2V	Yes/Yes	73%	45%	ç
References	Process	Start-up integration	Min. $V_{\rm TG}$ for cold-start	Start-up time	Min. $V_{\rm TG}$ for operation		Regulation / MPPT	Peak harv. efficiency	Efficiency @ low $V_{\rm TG}$	

(1) Estimated from transient plots

IEEE J Solid-State Circuits. Author manuscript; available in PMC 2022 June 01.

(2) Converter efficiency only.